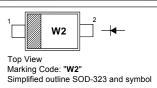
SILICON EPITAXIAL PLANAR SWITCHING DIODE

Features

Fast switching diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



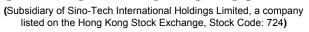
Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
	V_R	75	V
	V_{RM}	100	V
	l _F	250	mA
t = 1 µs t = 1 ms t = 1 s	I _{FSM}	2 1 0.5	A A A
	P _{tot}	200	mW
	T _j	150	°C
	T_{stg}	- 65 to + 150	°C
	t = 1 ms	V_{R} V_{RM} I_{F} $t = 1 \mu s$ $t = 1 ms$ $t = 1 s$ P_{tot} T_{j}	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Characteristics at Ta = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 50$ mA at $I_F = 150$ mA	V _F	0.715 0.855 1 1.25	V
Reverse Leakage Current at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}$, $T_J = 150 ^{\circ}\text{C}$ at $V_R = 75 \text{ V}$, $T_J = 150 ^{\circ}\text{C}$	I _R	1 30 50	μΑ
Diode Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C _{tot}	2	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$, $I_R = 1 \text{ mA}$, $R_L = 100 \Omega$	t _{rr}	6	ns





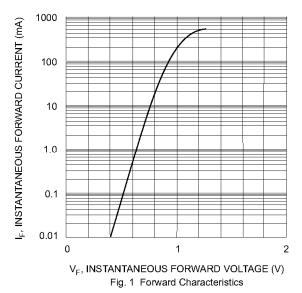


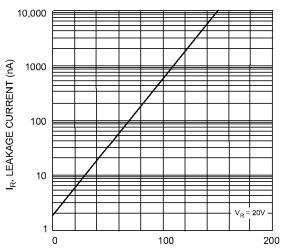






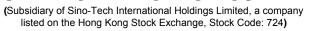






 $\label{eq:total_total_total} \textbf{T}_{j}, \text{JUNCTION TEMPERATURE (°C)} \\ \text{Fig. 2 Leakage Current vs Junction Temperature}$















PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

